

In the Claims:

Claims 1-42 (Cancelled).

43. (Original) A thin film transistor backplane, comprising:
- a polyimide substrate;
 - a first passivation layer deposited on a deposition surface of the polyimide substrate;
 - an array of gate electrodes and gate lines patterned on the passivation layer;
 - a gate insulating layer deposited over the array of gate electrodes and gate lines;
 - a semiconducting channel layer deposited over the gate insulating layer;
 - a contact layer deposited on and in contact with the channel layer; and
 - an array of source electrodes, drain electrodes, lines and pads fabricated on and in contact with the contact layer.

Claims 44-95 (Cancelled).